

MDL-III-830L/1~120mW

INFRARED DIODE LASER AT 830nm





Infrared diode laser at 830nm is made features of round spot, long lifetime, low cost and easy operating, which is widely used in measurement, spectrum analysis, etc.



SPECIFICATIONS

Wavelength (nm)	830 ± 10		
Output power (mW)	>1, 5, 10, ..., 120		
Spectral line width (nm)	<0.5		
Transverse mode	Near TEM ₀₀		
Operating mode	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%		
Warm-up time (minutes)	<5		
Beam divergence, full angle (mrad)	<1.0		
Dimensions of beam at the aperture (mm)	~3.0		
Beam height from base plate (mm)	24.8		
Operating temperature (°C)	10~35		
Power supply (90-264VAC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
Modulation option	TTL/Analog 1Hz-5KHz, 1Hz-10KHz, 1Hz-30KHz, and TTL on/off		
Expected lifetime (hours)	10000		
Warranty	1 year		



MxL-III-830	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
 139(L)×73(W)×46.2(H) mm ³ , 0.6kg	 153 (L) ×155(W) ×92 (H) mm ³ , 1.5kg	 133 (L) ×130(W) ×65 (H) mm ³ , 1.2kg	 100 (L) ×62(W) ×56 (H) mm ³ , 0.2kg
